

P-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY

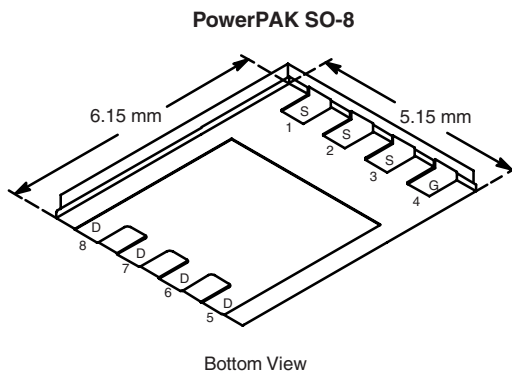
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
- 60	0.0145 at $V_{GS} = - 10$ V	- 14.4
	0.019 at $V_{GS} = - 4.5$ V	- 12.6

FEATURES

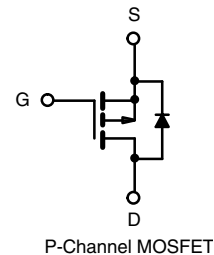
- TrenchFET® Power MOSFET
- Low Thermal Resistance PowerPAK® Package with Low 1.07 mm Profile



RoHS
COMPLIANT



Ordering Information: Si7461DP-T1-E3 (Lead (Pb)-free)



ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	10 sec	Steady State	Unit
Drain-Source Voltage	V_{DS}	- 60		V
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^a	I_D	- 14.4	- 8.6	A
		- 11.5	- 6.9	
Pulsed Drain Current	I_{DM}	- 60		
Continuous Source Current (Diode Conduction) ^a	I_S	- 4.5	- 1.6	
Avalanche Current	I_{AS}	50		W
Single Pulse Avalanche Energy	E_{AS}	125		
Maximum Power Dissipation ^a	P_D	5.4	1.9	W
		3.4	1.2	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150		$^\circ\text{C}$
Soldering Recommendations (Peak Temperature) ^{b,c}		260		

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	R_{thJA}	18	23	$^\circ\text{C/W}$
		52	65	
Maximum Junction-to-Case (Drain)	R_{thJC}	1.0	1.3	

Notes:

a. Surface Mounted on 1" x 1" FR4 Board.

b. See Solder Profile (<http://www.vishay.com/ppg?73257>). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

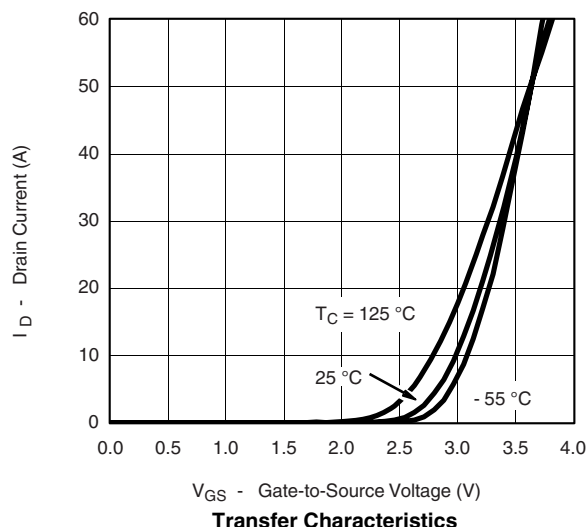
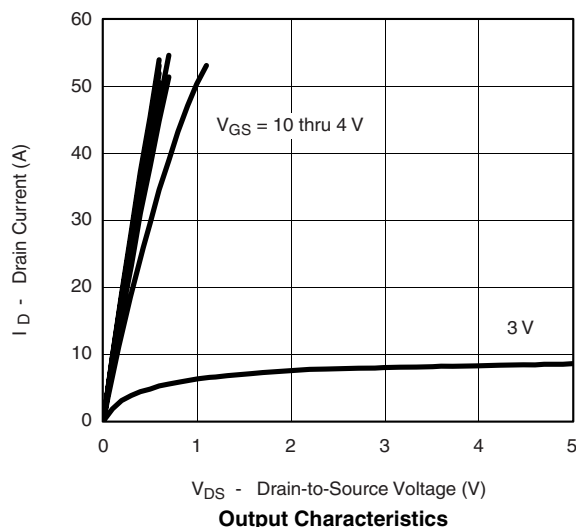
SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250\text{ }\mu\text{A}$	-1		-3	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -60\text{ V}$, $V_{GS} = 0\text{ V}$			-1	μA
		$V_{DS} = -60\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 70\text{ }^{\circ}\text{C}$			-10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \leq -5\text{ V}$, $V_{GS} = -10\text{ V}$	-40			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = -10\text{ V}$, $I_D = -14.4\text{ A}$		0.0115	0.0145	Ω
		$V_{GS} = -4.5\text{ V}$, $I_D = -12.6\text{ A}$		0.015	0.019	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -15\text{ V}$, $I_D = -14.4\text{ A}$		31		S
Diode Forward Voltage ^a	V_{SD}	$I_S = -4.5\text{ A}$, $V_{GS} = 0\text{ V}$		-0.8	-1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -30\text{ V}$, $V_{GS} = -10\text{ V}$, $I_D = -14.4\text{ A}$		121	190	nC
Gate-Source Charge	Q_{gs}			20		
Gate-Drain Charge	Q_{gd}			32		
Gate Resistance	R_g			3		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -30\text{ V}$, $R_L = 30\text{ }\Omega$ $I_D \cong -1\text{ A}$, $V_{GEN} = -10\text{ V}$, $R_G = 6\text{ }\Omega$		20	30	ns
Rise Time	t_r			20	30	
Turn-Off Delay Time	$t_{d(off)}$			205	310	
Fall Time	t_f			90	135	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = -4.5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$		45	70	

Notes:

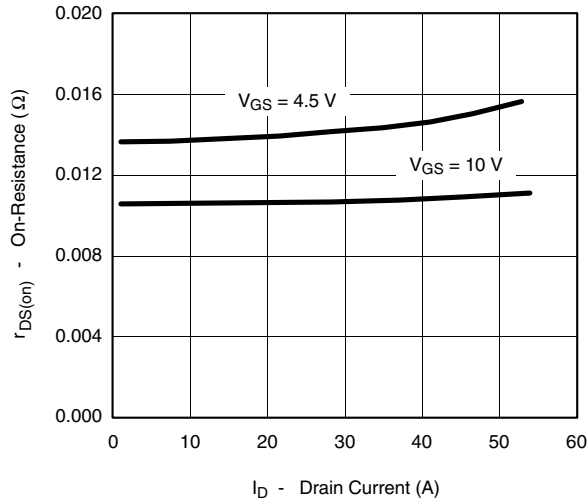
a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

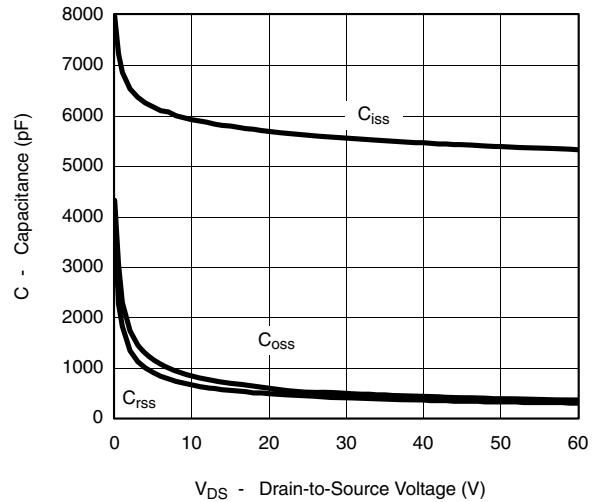
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS $25\text{ }^{\circ}\text{C}$, unless otherwise noted

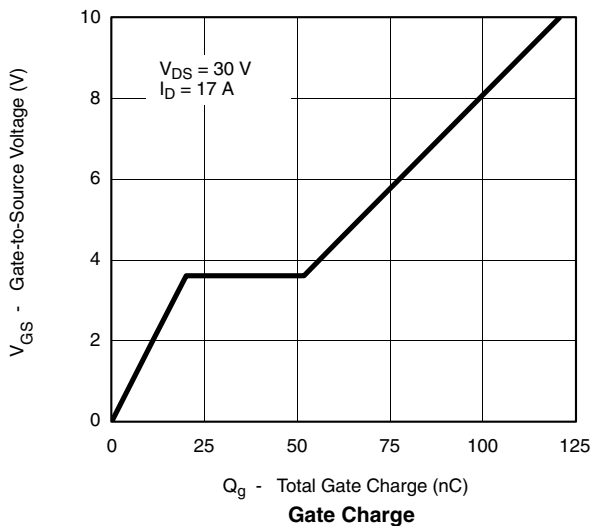
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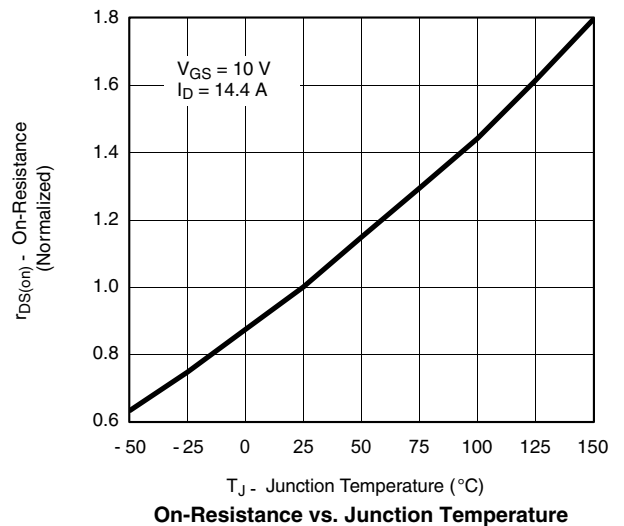
On-Resistance vs. Drain Current



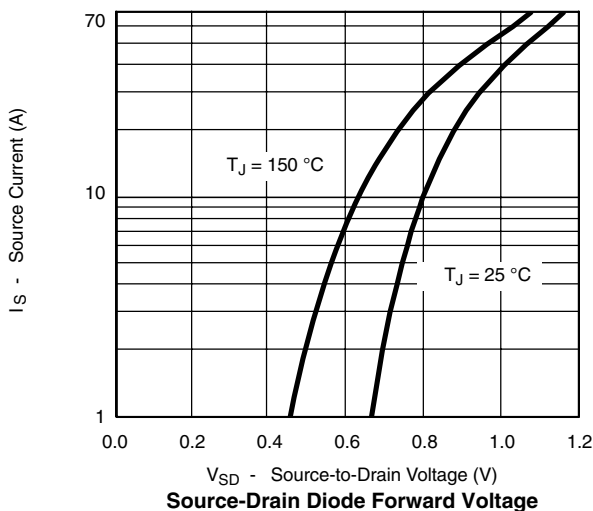
Capacitance



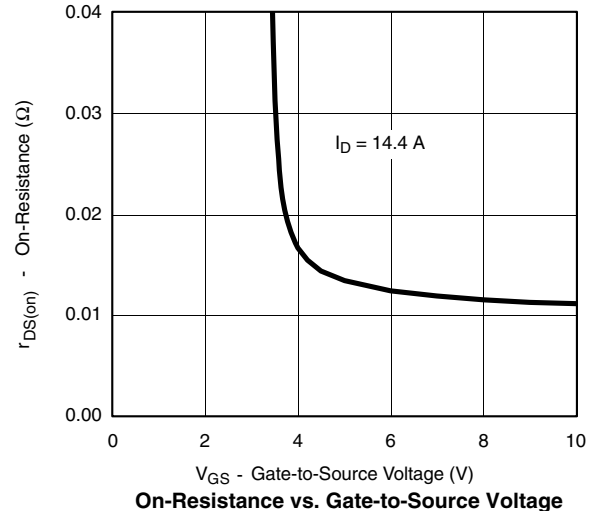
Gate Charge



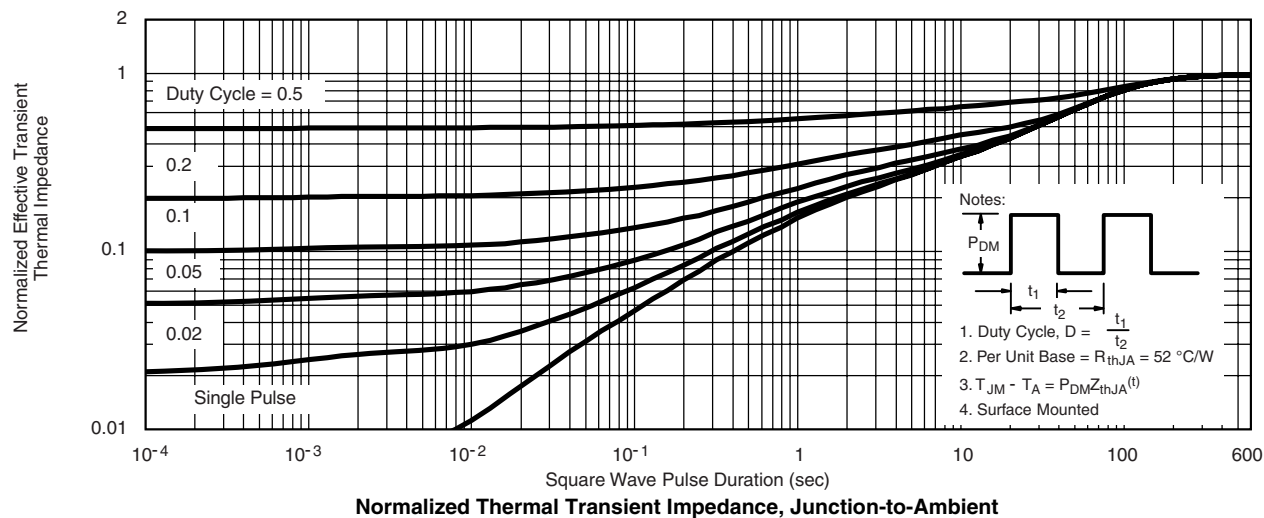
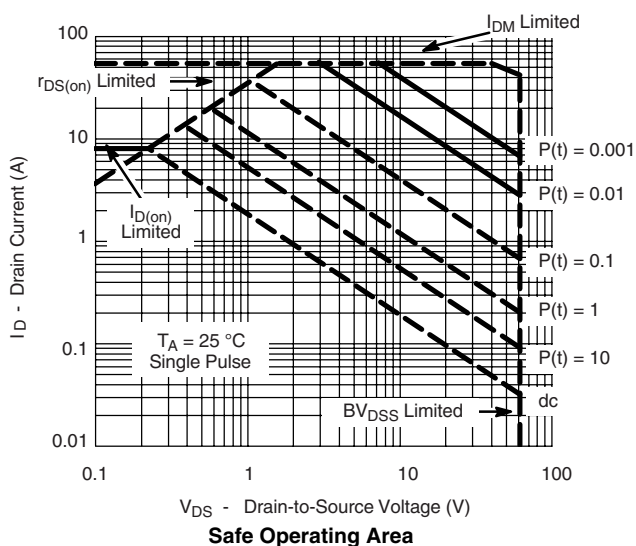
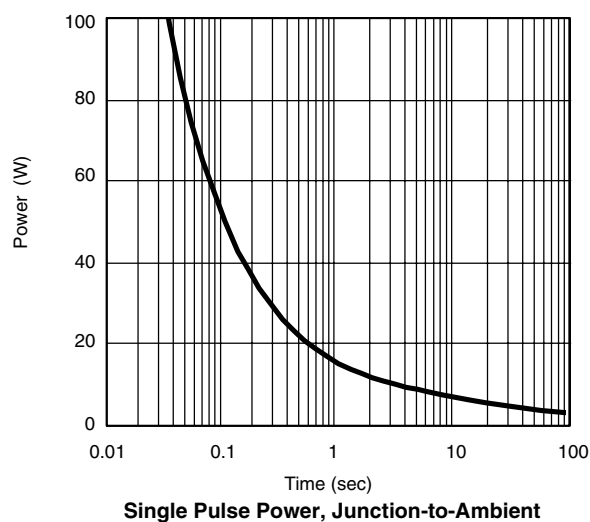
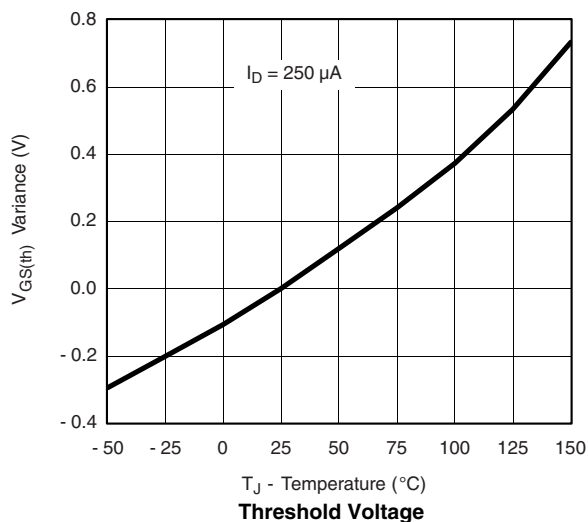
On-Resistance vs. Junction Temperature



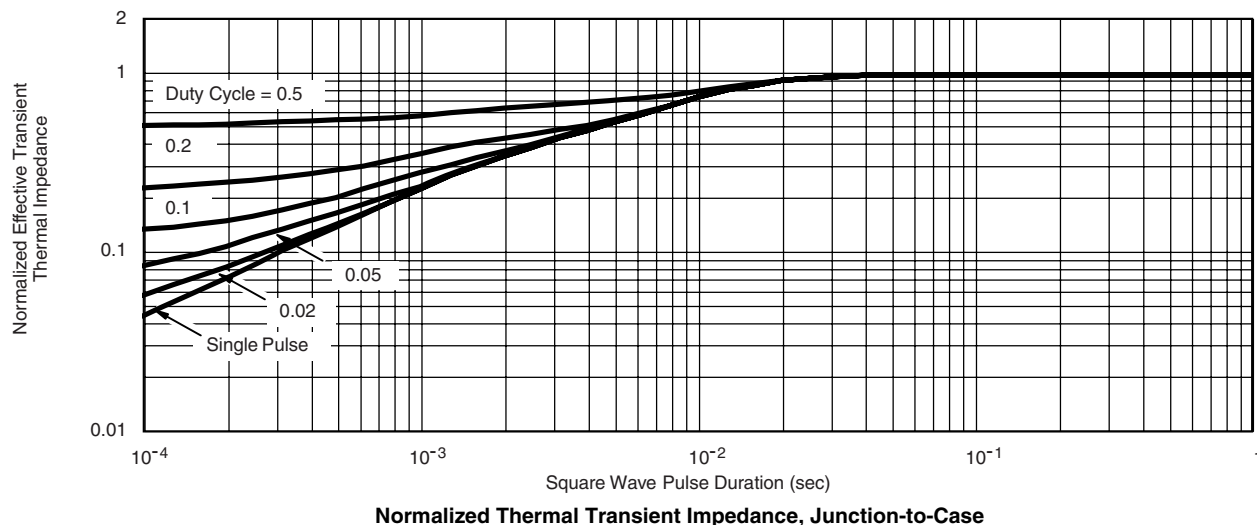
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

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